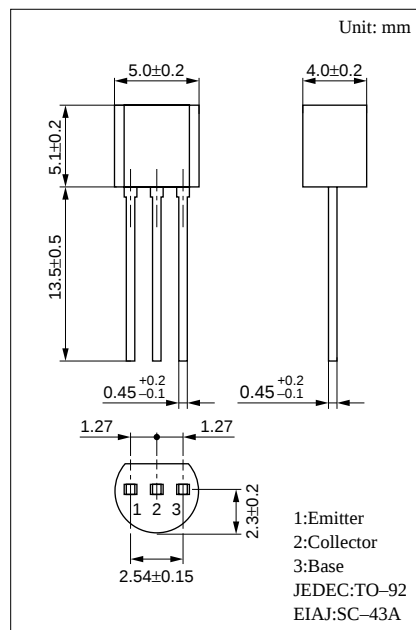


## Silicon PNP epitaxial planer type

Complementary to 2SC1473

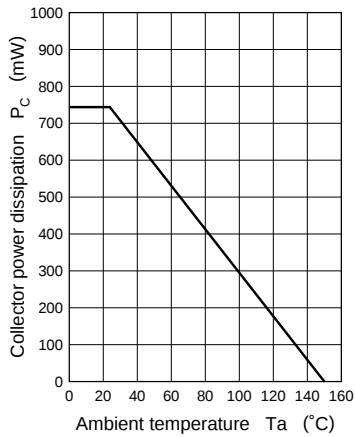
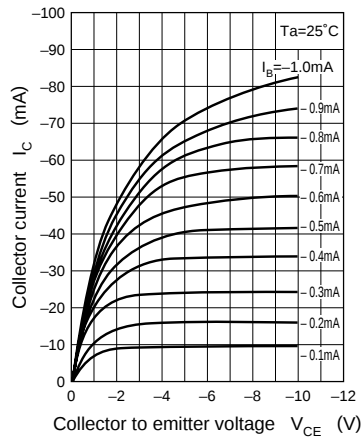
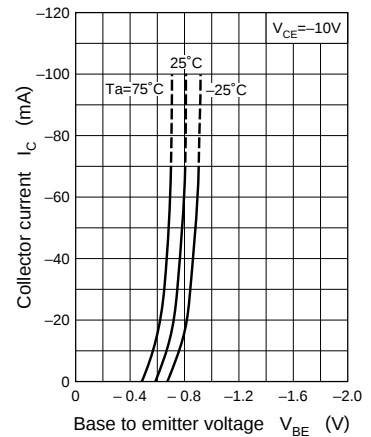
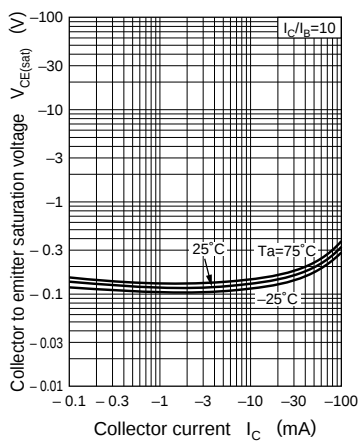
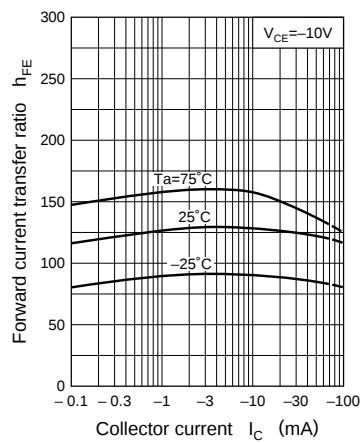
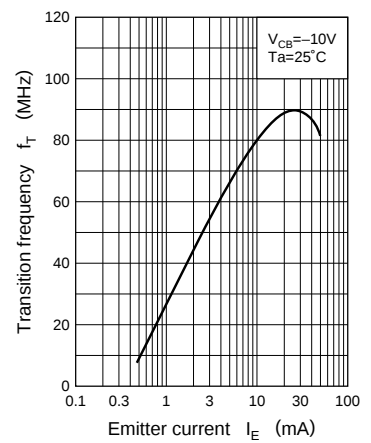
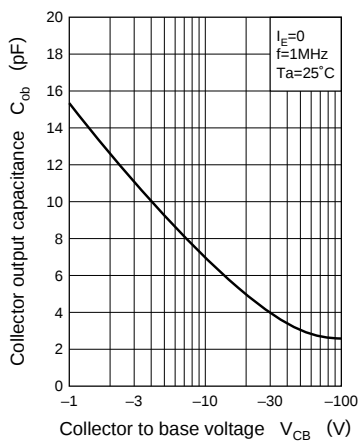
- High collector to emitter voltage  $V_{CEQ}$ .

| Parameter                    | Symbol    | Ratings    | Unit |
|------------------------------|-----------|------------|------|
| Collector to base voltage    | $V_{CBO}$ | −250       | V    |
| Collector to emitter voltage | $V_{CEO}$ | −200       | V    |
| Emitter to base voltage      | $V_{EBO}$ | −5         | V    |
| Peak collector current       | $I_{CP}$  | −100       | mA   |
| Collector current            | $I_C$     | −70        | mA   |
| Collector power dissipation  | $P_C$     | 750        | mW   |
| Junction temperature         | $T_j$     | 150        | °C   |
| Storage temperature          | $T_{stg}$ | −55 ~ +150 | °C   |



| Parameter                               | Symbol        | Conditions                                   | min  | typ | max  | Unit    |
|-----------------------------------------|---------------|----------------------------------------------|------|-----|------|---------|
| Collector cutoff current                | $I_{CEO}$     | $V_{CE} = -120V, I_B = 0, T_a = 60^{\circ}C$ |      |     | -1   | $\mu A$ |
| Collector to emitter voltage            | $V_{CEO}$     | $I_C = -100\mu A, I_B = 0$                   | -200 |     |      | V       |
| Emitter to base voltage                 | $V_{EBO}$     | $I_E = -1\mu A, I_C = 0$                     | -5   |     |      | V       |
| Forward current transfer ratio          | $h_{FE}^*$    | $V_{CE} = -10V, I_C = -5mA$                  | 60   |     | 220  |         |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -50mA, I_B = -5mA$                    |      |     | -1.5 | V       |
| Transition frequency                    | $f_T$         | $V_{CB} = -10V, I_E = 10mA, f = 200MHz$      | 50   |     |      | MHz     |
| Collector output capacitance            | $C_{ob}$      | $V_{CB} = -10V, I_E = 0, f = 1MHz$           |      |     | 10   | pF      |

| Rank     | Q        | R         |
|----------|----------|-----------|
| $h_{FE}$ | 60 ~ 150 | 100 ~ 220 |

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$  $I_{CEO} - T_a$ 